

WSP6077

Dual P-Ch MOSFET

General Description

The WSP6077 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP6077 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

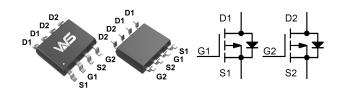
Product Summery

BVDSS	RDSON	ID
-60V	60mΩ	-8A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP8 Pin Configuration



Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	-60	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$ -8.0		A	
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-4.5	A	
I _{DM}	Pulsed Drain Current ² -30		А	
P _D @T _C =25℃	Total Power Dissipation ³ 1.5		W	
T _{STG}	Storage Temperature Range	ange -55 to 150		
TJ	Operating Junction Temperature Range -55 to 150		°C	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{eja}	Thermal Resistance Junction-Ambient ¹		70	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		35	°C/W

Absolute Maximum Ratings



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Electrical Characteristics (T_J=25⁻¹C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.02		V/℃
Б	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-5A		60	80	mΩ
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-2A		64	100	
V _{GS(th)}	Gate Threshold Voltage		-1.0	-1.5	-2.5	V
	V _{GS(th)} Temperature Coefficient	$V_{GS} = V_{DS}$, $I_D = -2500A$		4.32		mV/°C
	Drain-Source Leakage Current	V_{DS} =-52V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			-1	
I _{DSS}		V_{DS} =-52V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			-5	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm20V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-5A		15		S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		13	30	Ω
Qg	Total Gate Charge (-4.5V)			10		nC
Q _{gs}	Gate-Source Charge	V _{DS} =-30V , V _{GS} =-4.5V , I _D =-5A		3.2		
Q _{gd}	Gate-Drain Charge			2.5		
T _{d(on)}	Turn-On Delay Time			21		
Tr	Rise Time	V _{DD} =-30V , V _{GS} =-10V ,		19		
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω I _D =-1A		55		ns -
T _f	Fall Time			7.0		
Ciss	Input Capacitance			1400		
C _{oss}	Output Capacitance	V _{DS} =-30V , V _{GS} =0V , f=1MHz		95		pF
C _{rss}	Reverse Transfer Capacitance			70		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,4}	$-V_G=V_D=0V$, Force Current			-8	А
I _{SM}	Pulsed Source Current ^{2,4}				-30	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

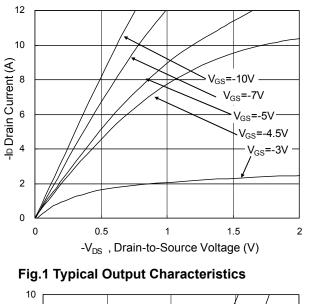
3.The power dissipation is limited by 150 $^\circ\!\!\mathbb{C}$ junction temperature

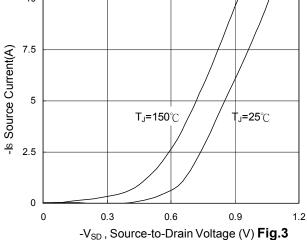
4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



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Typical Characteristics







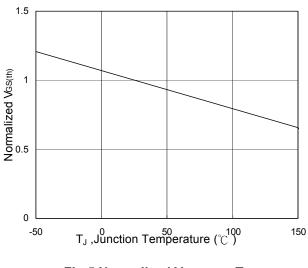


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

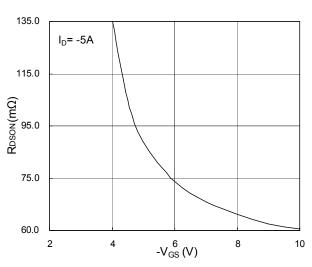
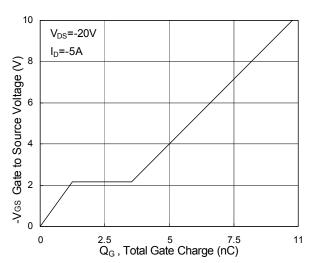
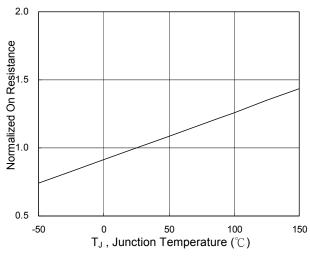
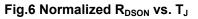


Fig.2 On-Resistance vs. G-S Voltage









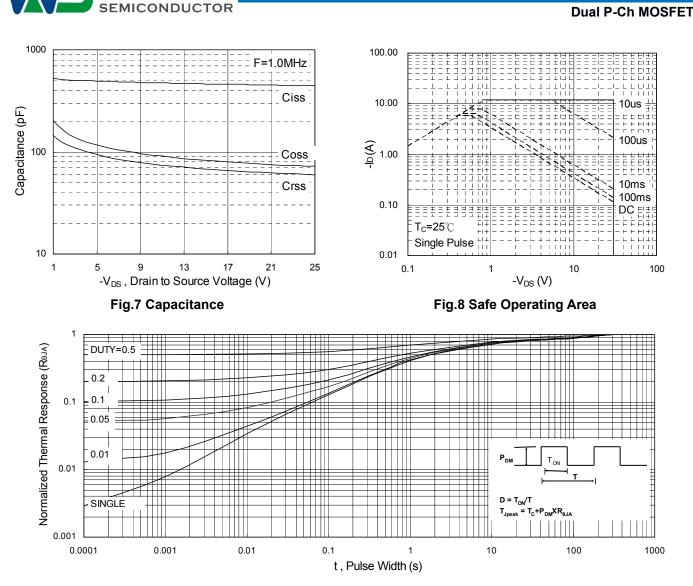
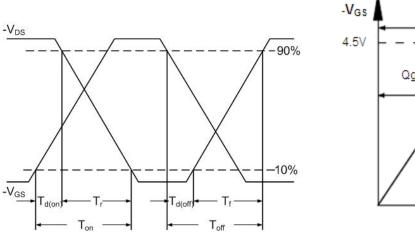


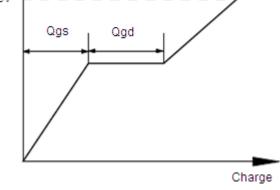
Fig.9 Normalized Maximum Transient Thermal Impedance





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WSP6077



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